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(Use as many sheets as necessary)

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	Complete If Known	
Application Number	10/602,716-Conf. #9955	
Filing Date	June 25, 2003	
First Named Inventor	Chandra Mouli	
Art Unit	2811	
Examiner Name	D. Kang Colleen matthews	
Attorney Dockel Number	M4065.0904/P904	

U.S. PATENT DOCUMENTS					
Examiner Initials*	Cite No.1	Document Number Number-Kind Code ² (# known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
CAM	AA	2002/0190287	12/19/2002	Mann et al.	

	FOREIGN PATENT DOCUMENTS					
Examiner Initials*	Cite No.	Foreign Patent Document Country Code ³ -Number ⁴ -Kind Code ³ (if known)	Publication Date MM-DD-YYYY	Name of Patentce or Applicant of Cited Document	Pagas, Columns, Lines, Whore Relevant Passages or Relevant Figures Appear	7°
CAM	BA	EP 0 798 785	10/01/1997			
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NON PATENT LITERATURE DOCUMENTS				
Examiner Initials	Cite No.1	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T 2	
CAM	CA	Kim, K.T. et al. – "Tungsten Silicide/Titanium Nitride Compound Gate," June 4, 1990, Symposium on VLSI Technology, Honolulu, June 4-7, 1990, New York, IEEE, US, pgs 115- 116.		
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CIAM	CE	International Search Report dated 11/30/2004.		

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